

CMOS SERIAL E²PROM

S-93C46A/56A/66A

The S-93C46A/56A/66A is high speed, low power 1K/2K/4K-bit E²PROM with a wide operating voltage range. It is organized as 64-word ×16-bit, 128-word×16-bit, 256-word×16-bit, respectively. Each is capable of sequential read, at which time addresses are automatically incremented in 16-bit blocks. The instruction code is compatible with the NM93CS46/56/66.

■ Features

- Low power consumption
 - Standby : 1.0 μA Max. (V_{CC}=5.5 V)
 - Operating : 0.8 mA Max. (V_{CC}=5.5 V)
 - : 0.4 mA Max. (V_{CC}=2.5 V)
- Wide operating voltage range
 - Read/Write : 1.8 to 5.5 V
- Sequential read capable
- Endurance : 10⁶ cycles/word
- Data retention : 10 years
- S-93C46A : 1K bits NM93CS46 instruction code compatible
- S-93C56A : 2K bits NM93CS56 instruction code compatible
- S-93C66A : 4K bits NM93CS66 instruction code compatible

■ Packages

- 8-pin DIP (PKG drawing code : DP008-A)
- 8-pin SOP (PKG drawing code : FJ008-D)
- 8-pin TSSOP (PKG drawing code : FT008-E)
- 8-pin MSOP (PKG drawing code : FN008-A)

■ Pin Assignment

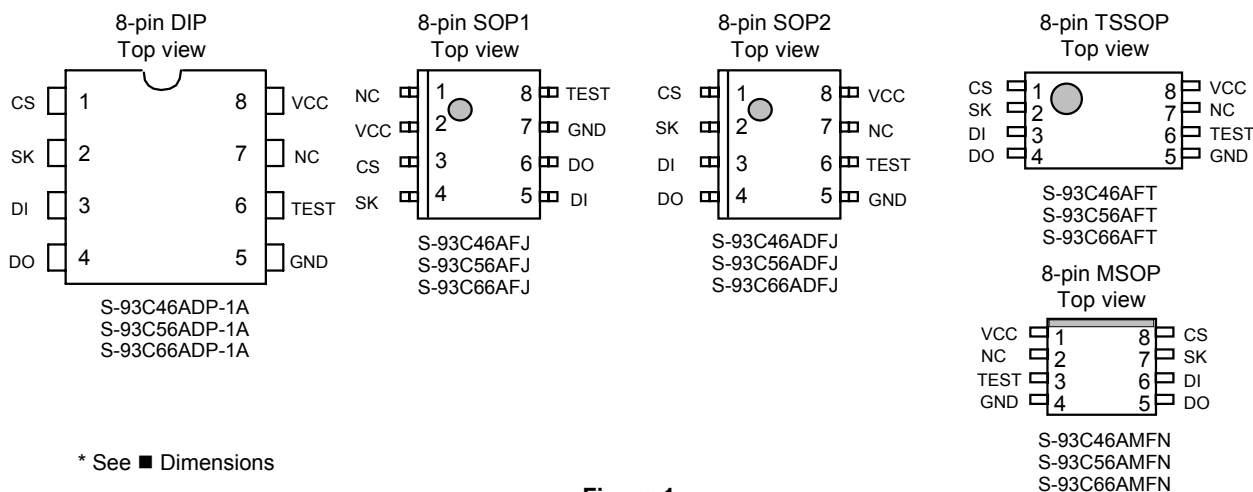


Figure 1

■ Pin Functions

Table 1

Name	Pin Number					Function
	DIP	SOP1	SOP2	TSSOP	MSOP	
CS	1	3	1	1	8	Chip select input
SK	2	4	2	2	7	Serial clock input
DI	3	5	3	3	6	Serial data input
DO	4	6	4	4	5	Serial data output
GND	5	7	5	5	4	Ground
TEST	6	8	6	6	3	Test pin (normally kept open) (can be connected to GND or V _{CC})
NC	7	1	7	7	2	No Connection
V _{CC}	8	2	8	8	1	Power supply

■ Block Diagram

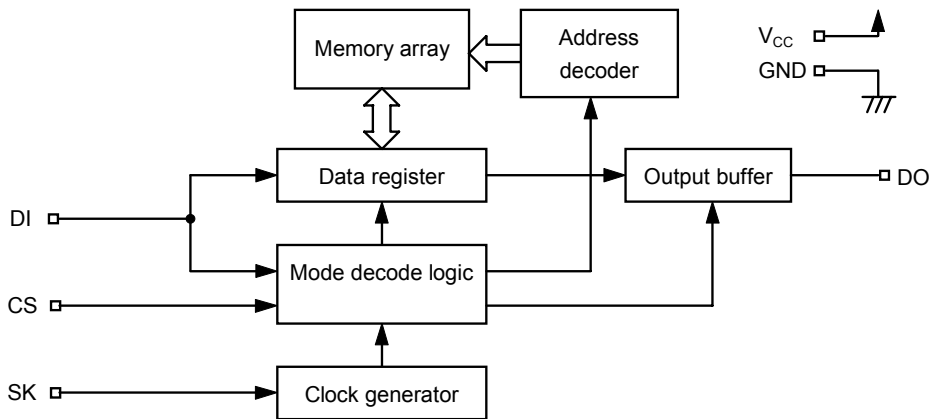


Figure 2

■ Instruction Set

Table 2

Instruction	Start Bit	Op Code	Address			Data
			S-93C46A	S-93C56A	S-93C66A	
READ (Read data)	1	10	A ₅ to A ₀	XA ₆ to A ₀	A ₇ to A ₀	D ₁₅ to D ₀ Output*1
WRITE (Write data)	1	01	A ₅ to A ₀	XA ₆ to A ₀	A ₇ to A ₀	D ₁₅ to D ₀ Input
ERASE (Erase data)	1	11	A ₅ to A ₀	XA ₆ to A ₀	A ₇ to A ₀	—
WRAL (Write all)*2	1	00	01xxxx	01xxxxxx	01xxxxxx	D ₁₅ to D ₀ Input
ERAL (Erase all)*2	1	00	10xxxx	10xxxxxx	10xxxxxx	—
EWEN (Program enable)	1	00	11xxxx	11xxxxxx	11xxxxxx	—
EWDS (Program disable)	1	00	00xxxx	00xxxxxx	00xxxxxx	—

x : Doesn't matter.

*1: Addresses are continuously incremented.

*2: Valid only at V_{CC} = 2.5 V to 5.5 V.

■ Absolute Maximum Ratings

Table 3

Parameter	Symbol	Ratings	Unit
Power supply voltage	V _{CC}	-0.3 to +7.0	V
Input voltage	V _{IN}	-0.3 to V _{CC} +0.3	V
Output voltage	V _{OUT}	-0.3 to V _{CC}	V
Operating ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature under bias	T _{bias}	-50 to +95	°C
Storage temperature	T _{stg}	-65 to +150	°C

■ Recommended Operating Conditions

Table 4

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Power supply voltage	V _{CC}	READ/WRITE/ERASE EWEN/EWDS	1.8	—	5.5	V
		WRAL/ERAL	2.5	—	5.5	V
		V _{CC} =4.5 to 5.5 V	2.0	—	V _{CC}	V
High level input voltage	V _{IH}	V _{CC} =2.7 to 4.5 V	0.8×V _{CC}	—	V _{CC}	V
		V _{CC} =1.8 to 2.7 V	0.8×V _{CC}	—	V _{CC}	V
		V _{CC} =4.5 to 5.5 V	0.0	—	0.8	V
Low level input voltage	V _{IL}	V _{CC} =2.7 to 4.5 V	0.0	—	0.2×V _{CC}	V
		V _{CC} =1.8 to 2.7 V	0.0	—	0.15×V _{CC}	V

■ Pin Capacitance

Table 5

(T_a=25 °C, f=1.0 MHz, V_{CC}=5 V)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Input Capacitance	C _{IN}	V _{IN} =0 V	—	—	8	pF
Output Capacitance	C _{OUT}	V _{OUT} =0 V	—	—	10	pF

■ Endurance

Table 6

Parameter	Symbol	Min.	Typ.	Max.	Unit
Endurance	N _w	10 ⁶	—	—	cycles/word

■ DC Electrical Characteristics

Table 7

Parameter	Smb1	Conditions	V _{CC} =4.5 V to 5.5 V			V _{CC} =2.5 V to 4.5 V			V _{CC} =1.8 to 2.5 V			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Current consumption (READ)	I _{CC1}	DO unloaded	—	—	0.8	—	—	0.6	—	—	0.4	mA
Current consumption (PROGRAM)	I _{CC2}	DO unloaded	—	—	2.0	—	—	1.5	—	—	1.0	mA

Table 8

Parameter	Smb1	Conditions	V _{CC} =4.5 V to 5.5 V			V _{CC} =2.5 to 4.5 V			V _{CC} =1.8 to 2.5 V			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
Standby current consumption	I _{SB}	CS=GND DO=Open Connected to V _{CC} or GND	—	—	1.0	—	—	0.6	—	—	0.4	μA
Input leakage current	I _{LI}	V _{IN} =GND to V _{CC}	—	0.1	1.0	—	0.1	1.0	—	0.1	1.0	μA
Output leakage current	I _{LO}	V _{OUT} =GND to V _{CC}	—	0.1	1.0	—	0.1	1.0	—	0.1	1.0	μA
Low level output voltage	V _{OL}	I _{OL} =2.1 mA	—	—	0.4							V
		I _{OL} =100 μA	—	—	0.1	—	—	0.1	—	—	0.1	V
High level output voltage	V _{OH}	I _{OH} =-400 μA	2.4	—	—							V
		I _{OH} =-100 μA	V _{CC} -0.7	—	—	V _{CC} -0.7	—	—				V
		I _{OH} =-10 μA	V _{CC} -0.7	—	—	V _{CC} -0.7	—	—	V _{CC} -0.2	—	—	V
Write enable latch data hold voltage	V _{DH}	Only when write disable mode	1.5	—	—	1.5	—	—	1.5	—	—	V

■ AC Electrical Characteristics

Table 9

Input pulse voltage	0.1×V _{CC} to 0.9×V _{CC}
Output reference voltage	0.5×V _{CC}
Output load	100pF

Table 10

Parameter	Smb1	V _{CC} =4.5 to 5.5V			V _{CC} =2.5 to 4.5 V			V _{CC} =1.8 to 2.5V			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
CS setup time	t _{CSS}	0.2	—	—	0.4	—	—	1.0	—	—	μs
CS hold time	t _{CSH}	0	—	—	0	—	—	0	—	—	μs
CS deselect time	t _{CDS}	0.2	—	—	0.2	—	—	0.4	—	—	μs
Data setup time	t _{DS}	0.1	—	—	0.2	—	—	0.4	—	—	μs
Data hold time	t _{DH}	0.1	—	—	0.2	—	—	0.4	—	—	μs
Output delay	t _{PD}	—	—	0.4	—	—	1.0	—	—	2.0	μs
Clock frequency	f _{SK}	0	—	2.0	0	—	0.5	—	—	0.25	MHz
Clock pulse width	t _{SKH} , t _{SKL}	0.25	—	—	1.0	—	—	2.0	—	—	μs
Output disable time	t _{HZ1} , t _{HZ2}	0	—	0.15	0	—	0.5	0	—	1.0	μs
Output enable time	t _{SV}	0	—	0.15	0	—	0.5	0	—	1.0	μs
Programming time	t _{PR}	—	4.0	10.0	—	4.0	10.0	—	4.0	10.0	ms

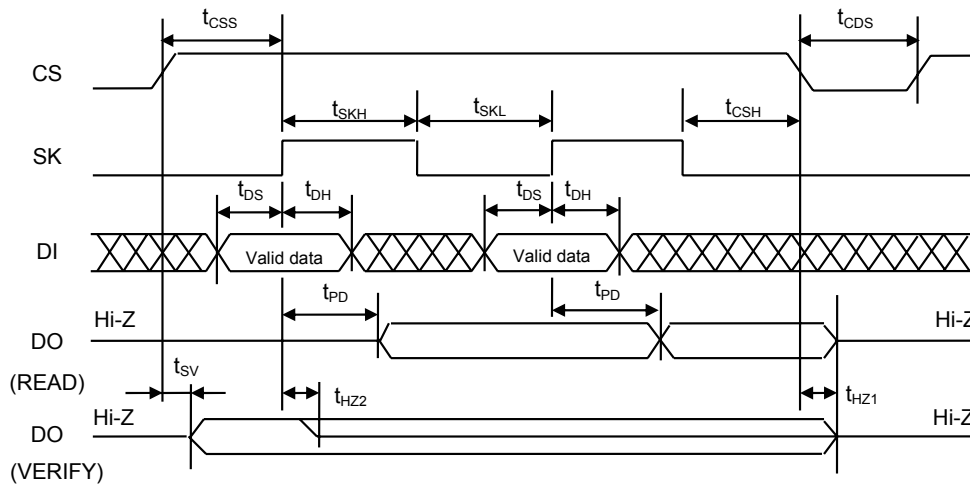


Figure 3 Read Timing

■ **Operation**

Instructions (in the order of start-bit, instruction, address, and data) are latched to DI in synchronization with the rising edge of SK after CS goes high. A start-bit can only be recognized when the high of DI is latched to the rising edge of SK when CS goes from low to high, it is impossible for it to be recognized as long as DI is low, even if there are SK pulses after CS goes high. Any SK pulses input while DI is low are called "dummy clocks." Dummy clocks can be used to adjust the number of clock cycles needed by the serial IC to match those sent out by the CPU. Instruction input finishes when CS goes low, where it must be low between commands during t_{CDS} .

All input, including DI and SK signals, is ignored while CS is low, which is stand-by mode.

1. Read

The READ instruction reads data from a specified address. After A0 is latched at the rising edge of SK, DO output changes from a high-impedance state (Hi-Z) to low level output. Data is continuously output in synchronization with the rise of SK.

When all of the data (D0) in the specified address has been read, the data in the next address can be read with the input of another SK clock. Thus, it is possible for all of the data addresses to be read through the continuous input of SK clocks as long as CS is high.

The last address ($A_n \dots A_1 A_0 = 1 \dots 11$) rolls over to the top address ($A_n \dots A_1 A_0 = 0 \dots 00$).

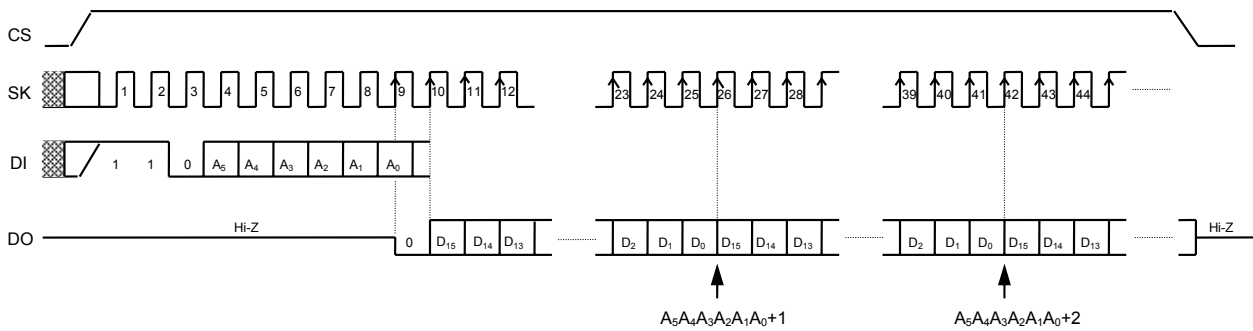


Figure 4 Read Timing (S-93C46A)

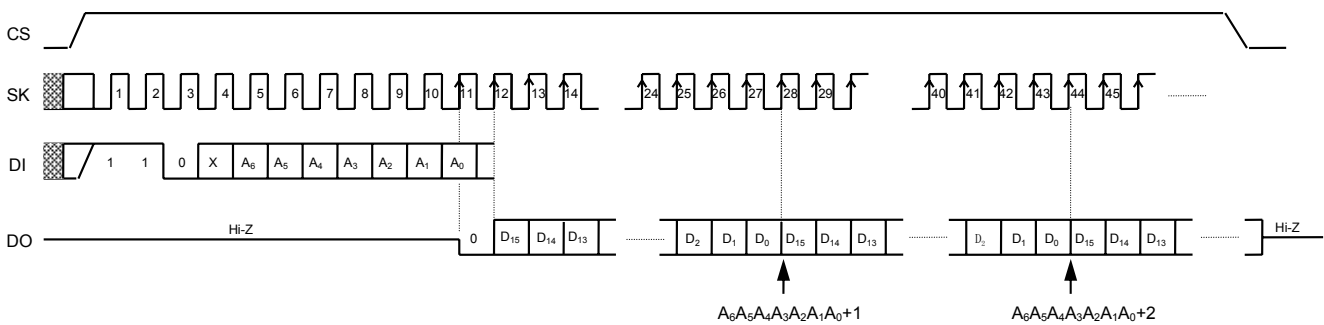


Figure 5 Read Timing (S-93C56A)

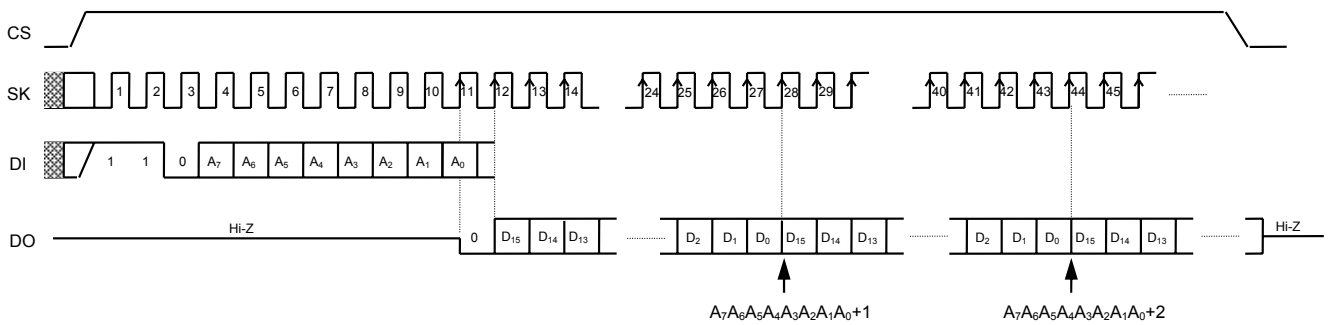


Figure 6 Read Timing (S-93C66A)

2. Write (WRITE, ERASE, WRAL, ERAL)

There are four write instructions, WRITE, ERASE, WRAL, and ERAL. Each automatically begins writing to the non-volatile memory when CS goes low at the completion of the specified clock input.

The write operation is completed in 10 ms (t_{PR} Max.), and the typical write period is less than 5 ms. In the S-93C46A/56A/66A, it is easy to VERIFY the completion of the write operation in order to minimize the write cycle by setting CS to high and checking the DO pin, which is low during the write operation and high after its completion. This VERIFY procedure can be executed over and over again.

Because all SK and DI inputs are ignored during the write operation, any input of instruction will also be disregarded. When DO outputs high after completion of the write operation or if it is in the high-impedance state (Hi-Z), the input of instructions is available. Even if the DO pin remains high, it will enter the high-impedance state upon the recognition of a high of DI (start-bit) attached to the rising edge of an SK pulse. (see Figure 3).

DI input should be low during the VERIFY procedure.

2.1 WRITE

This instruction writes 16-bit data to a specified address. After changing CS to high, input a start-bit, op-code (WRITE), address, and 16-bit data. If there is a data overflow of more than 16 bits, only the last 16 bits of the data is considered valid. Changing CS to low will start the WRITE operation. It is not necessary to make the data "1" before initiating the WRITE operation.

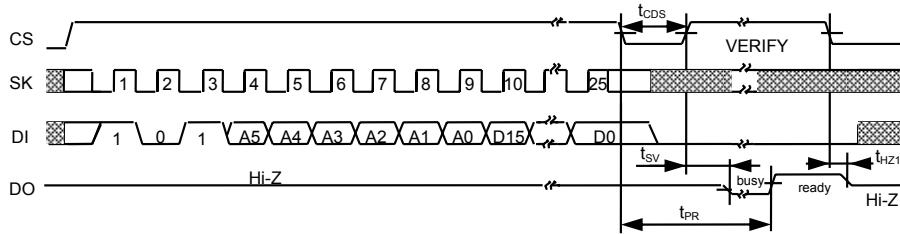


Figure 7 WRITE Timing (S-93C46A)

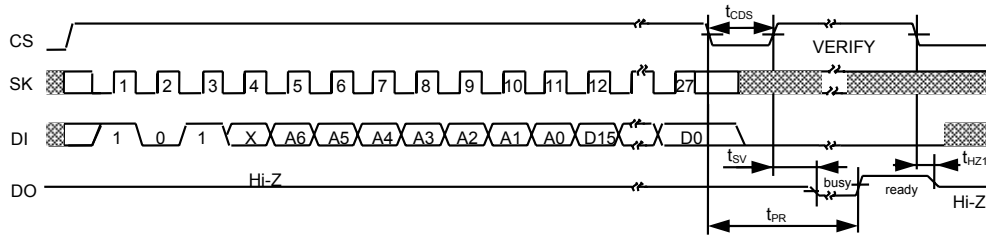


Figure 8 WRITE Timing (S-93C56A)

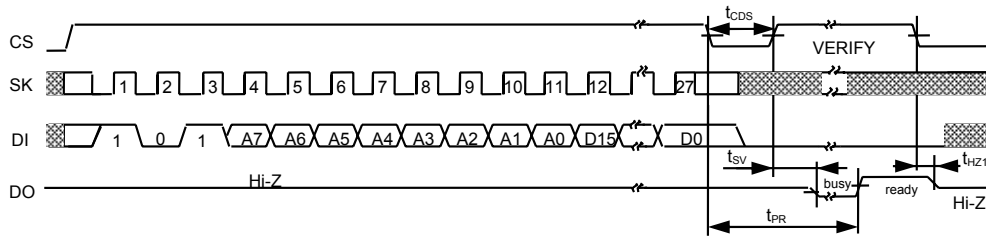


Figure 9 WRITE Timing (S-93C66A)

2.2 ERASE

This command erases 16-bit data in a specified address.

After changing CS to high, input a start-bit, op-code (ERASE), and address. It is not necessary to input data. Changing CS to low will start the ERASE operation, which changes every bit of the 16-bit data to "1."

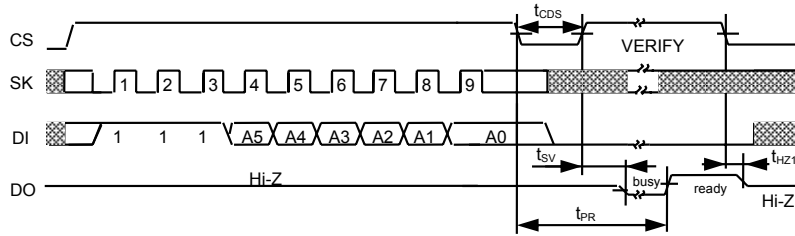


Figure 10 ERASE Timing (S-93C46A)

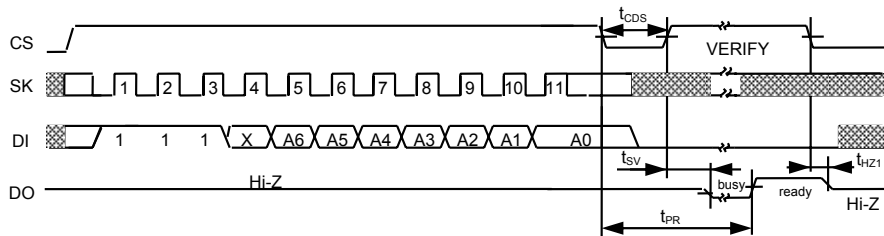


Figure 11 ERASE Timing (S-93C56A)

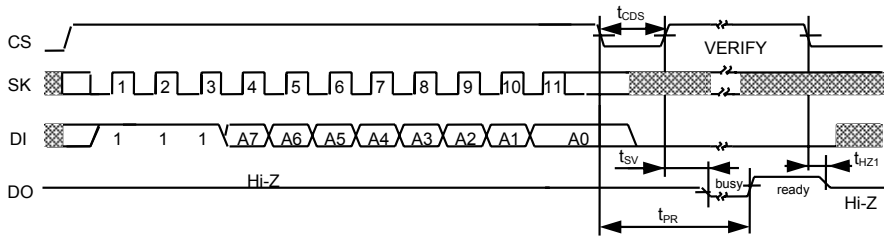


Figure 12 ERASE Timing (S-93C66A)

2.3 WRAL

This instruction writes the same 16-bit data into every address. After changing CS to high, input a start-bit, op-code (WRAL), address (optional), and 16-bit data. If there is a data overflow of more than 16 bits, only the last 16 bits of the data is considered valid. Changing CS to low will start the WRAL operation. It is not necessary to make the data "1" before initiating the WRAL operation.

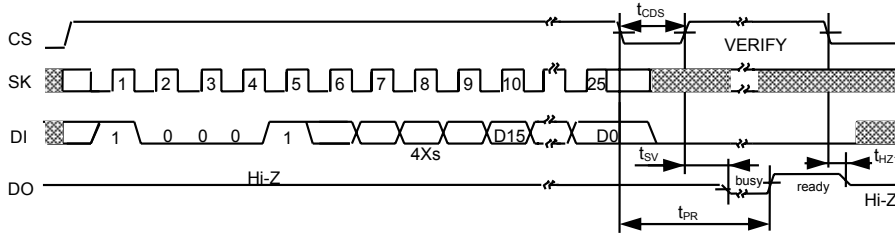


Figure 13 WRAL Timing (S-93C46A)

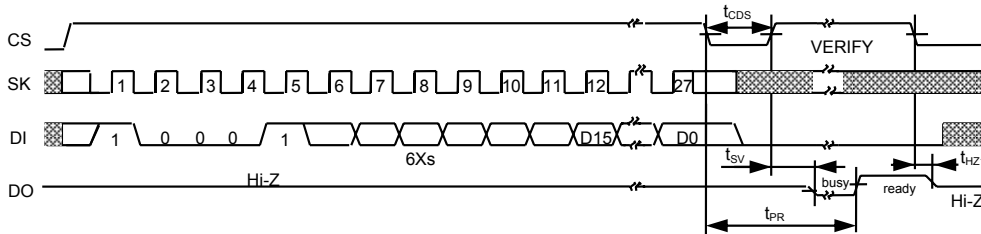


Figure 14 WRAL Timing (S-93C56A)

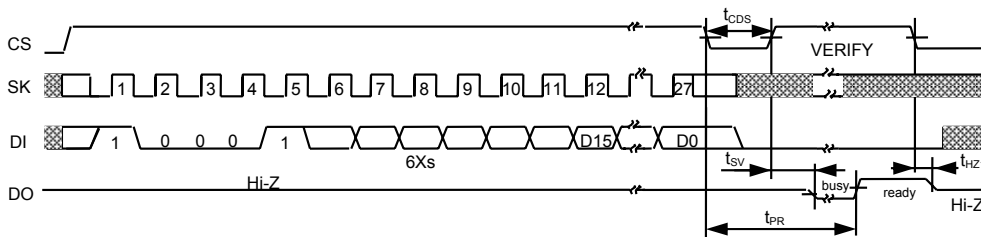


Figure 15 WRAL Timing (S-93C66A)

2.4 ERAL

This instruction erases the data in every address. After changing CS to high, input a start-bit, op-code (ERAL), and address (optional). It is not necessary to input data. Changing CS to low will start the ERAL operation, which changes every bit of data to "1."

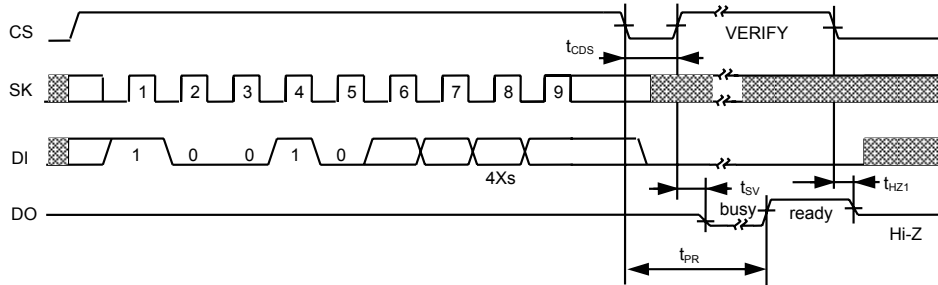


Figure 16 ERAL Timing (S-93C46A)

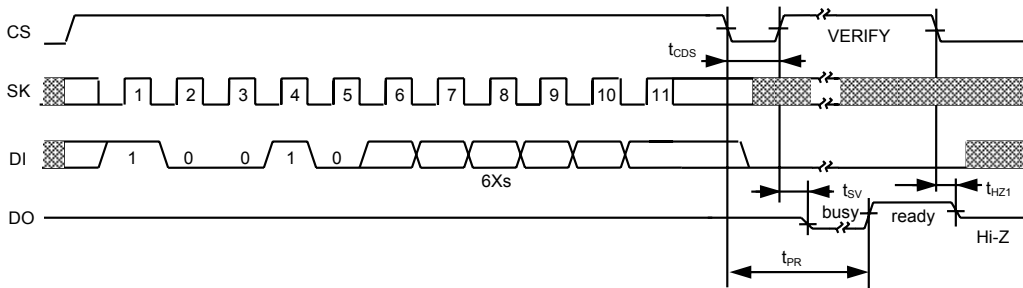


Figure 17 ERAL Timing (S-93C56A)

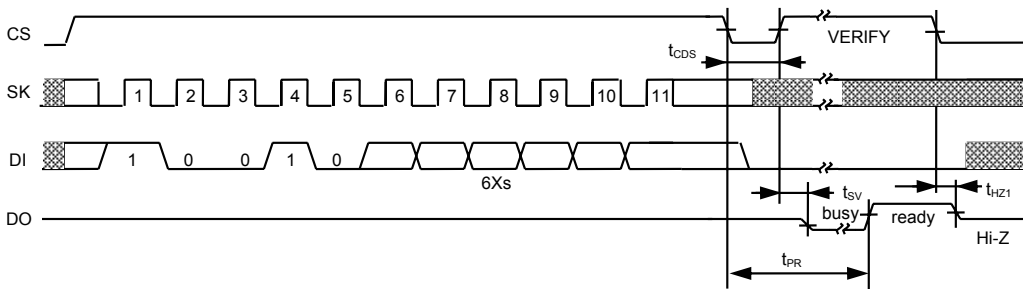


Figure 18 ERAL Timing (S-93C66A)

3. Write enable (EWEN) and Write disable (EWDS)

The EWEN instruction puts the S-93C46A/56A/66A into write enable mode, which accepts WRITE, ERASE, WRAL, and ERAL instructions. The EWDS instruction puts the S-93C46A/56A/66A into write disable mode, which refuses WRITE, ERASE, WRAL, and ERAL instructions.

The S-93C46A/56A/66A powers on in write disable mode, which protects data against unexpected, erroneous write operations caused by noise and/or CPU malfunctions. It should be kept in write disable mode except when performing write operations, after power-on and before shut-down.

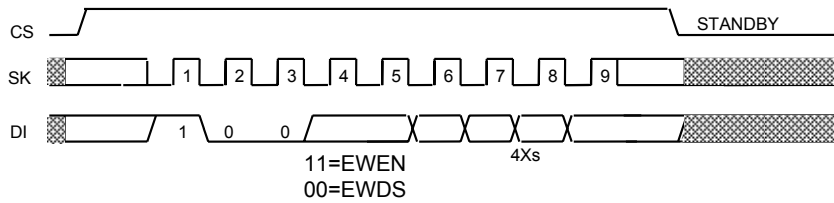


Figure 19 EWEN/EWDS Timing (S-93C46A)

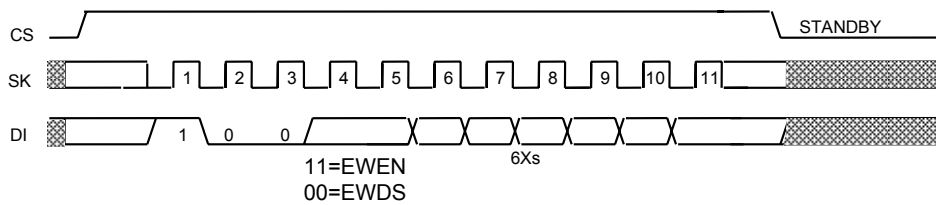


Figure 20 EWEN/EWDS Timing (S-93C56A)

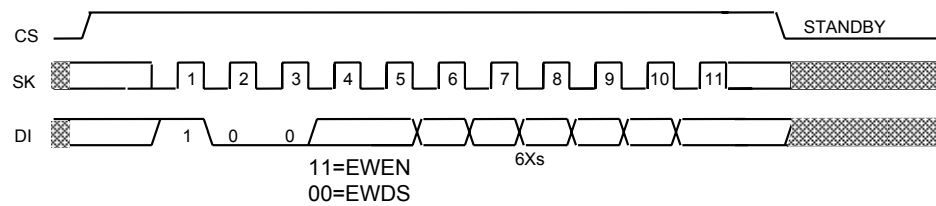


Figure 21 EWEN/EWDS Timing (S-93C66A)

■ **Receiving a Start-Bit**

Both the recognition of a start-bit and the VERIFY procedure occur when CS is “high”. Therefore, only after a write operation, in order to accept the next command by having CS go high, the DO pin switch from a state of high-impedence to a state of data output; but if it recognizes a start-bit, the DO pin returns to a state of high-impedence.

When a 3-wire interface is configured by connecting the DI input pin and DO output pin, a period in which the data output from the CPU and the serial memory collide may be generated, preventing successful input of the start bit.

■ **Three-wire Interface (DI-DO direct connection)**

Although the normal configuration of a serial interface is a 4-wire interface to CS, SK, DI, and DO, a 3-wire interface is also a possibility by connecting DI and DO. However, since there is a possibility that the DO output from the serial memory IC will interfere with the data output from the CPU with a 3-wire interface, install a resistor between DI and DO in order to give preference to data output from the CPU to DI (See Figure 22).

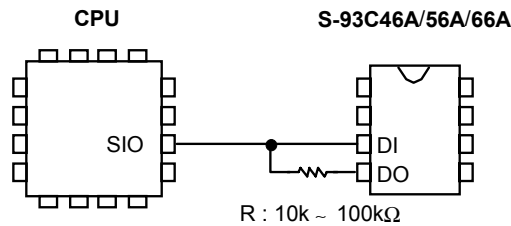


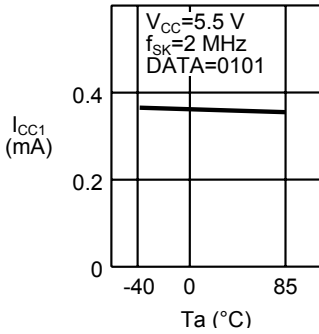
Figure 22

Please refer Application Note “S-29 & S-93C series EEPROMs Tips, Tricks & Traps” for equivalent circuit of each pin.

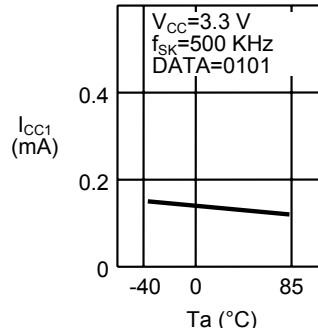
■ **Characteristics**

1. DC Characteristics

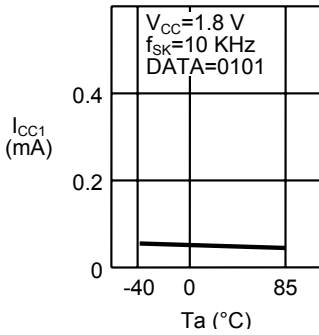
1.1 Current consumption (READ) I_{CC1} — Ambient temperature T_a



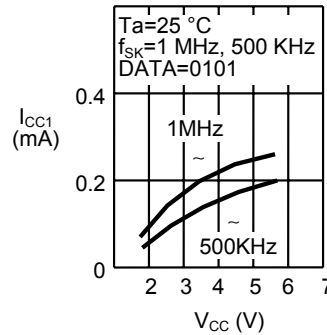
1.2 Current consumption (READ) I_{CC1} — Ambient temperature T_a



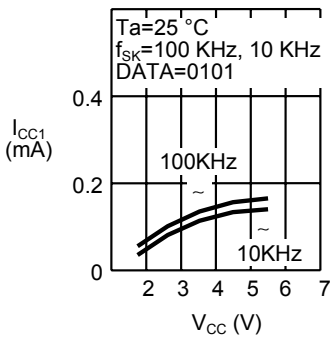
1.3 Current consumption (READ) I_{CC1} — Ambient temperature T_a



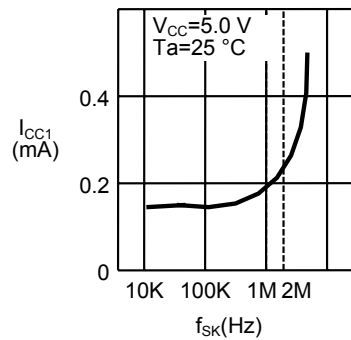
1.4 Current consumption (READ) I_{CC1} — Power supply voltage V_{CC}



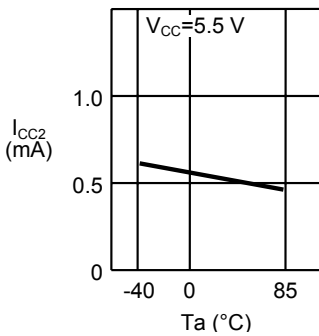
1.5 Current consumption (READ) I_{CC1} — Power supply voltage V_{CC}



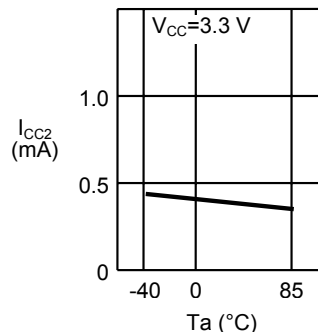
1.6 Current consumption (READ) I_{CC1} — Clock frequency f_{SK}



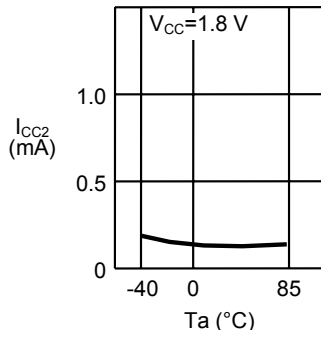
1.7 Current consumption (WRITE) I_{CC2} — Ambient temperature T_a



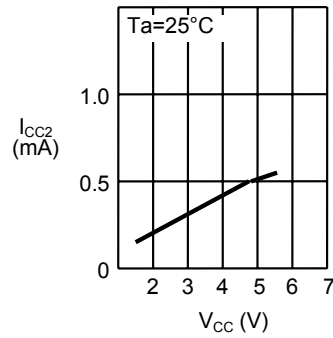
1.8 Current consumption (WRITE) I_{CC2} — Ambient temperature T_a



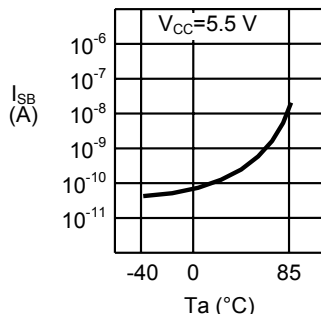
1.9 Current consumption (WRITE) I_{CC2} —
Ambient temperature T_a



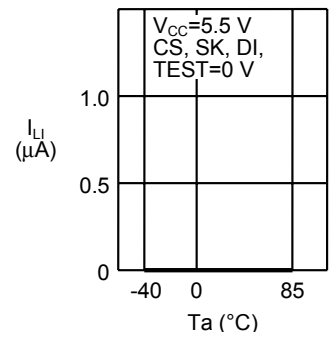
1.10 Current consumption (WRITE) I_{CC2} —
Power supply voltage V_{CC}



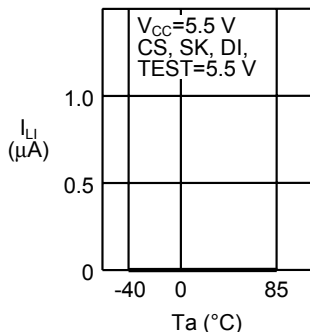
1.11 Standby current consumption I_{SB} —
Ambient temperature T_a



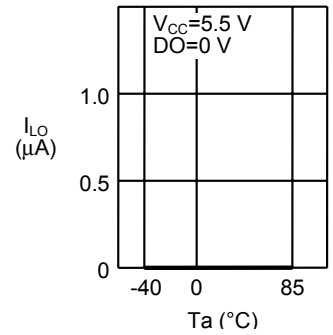
1.12 Input leakage current I_{LI} —
Ambient temperature T_a



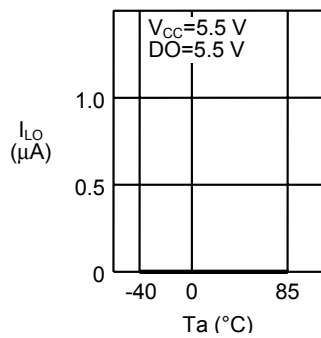
1.13 Input leakage current I_{LI} —
Ambient temperature T_a



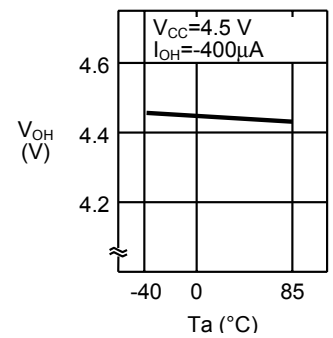
1.14 Output leakage current I_{LO} —
Ambient temperature T_a



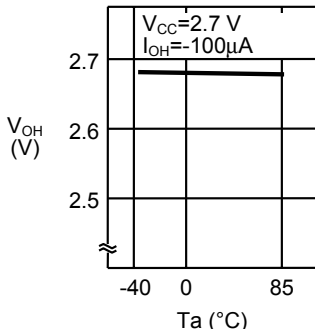
1.15 Output leakage current I_{LO} —
Ambient temperature T_a



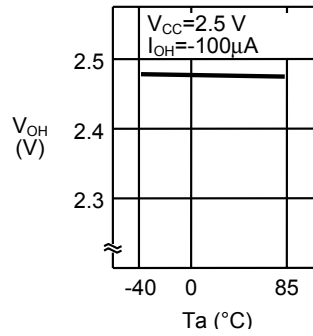
1.16 High level output voltage V_{OH} —
Ambient temperature T_a



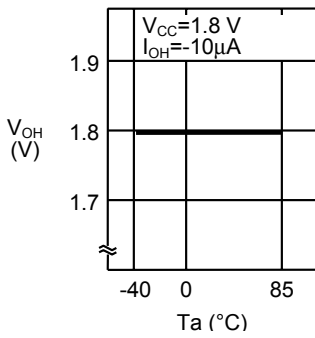
1.17 High level output voltage V_{OH}
Ambient temperature T_a



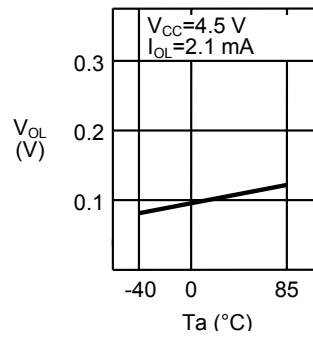
1.18 High level output voltage V_{OH}
Ambient temperature T_a



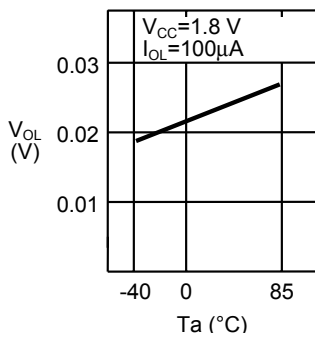
1.19 High level output voltage V_{OH}
Ambient temperature T_a



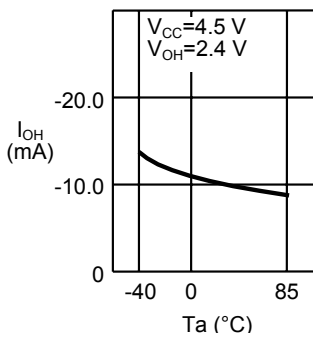
1.20 Low level output voltage V_{OL}
Ambient temperature T_a



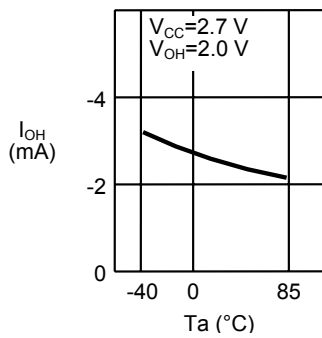
1.21 Low level output voltage V_{OL}
Ambient temperature T_a



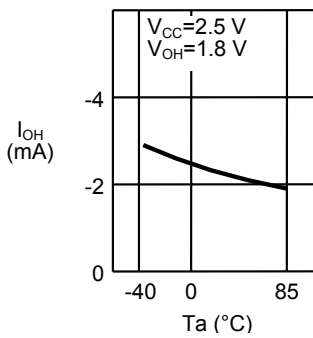
1.22 High level output current I_{OH}
Ambient temperature T_a



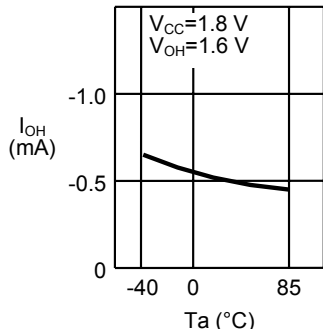
1.23 High level output current I_{OH}
Ambient temperature T_a



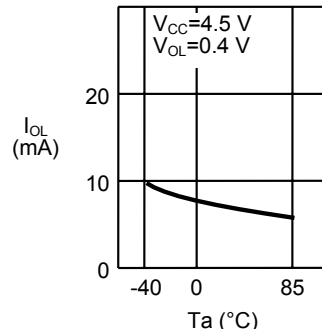
1.24 High level output current I_{OH}
Ambient temperature T_a



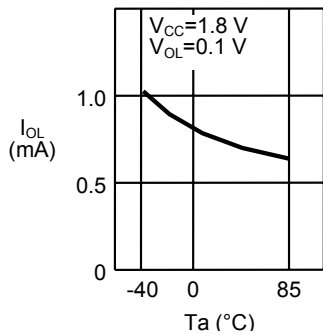
1.25 High level output current I_{OH} —
Ambient temperature T_a



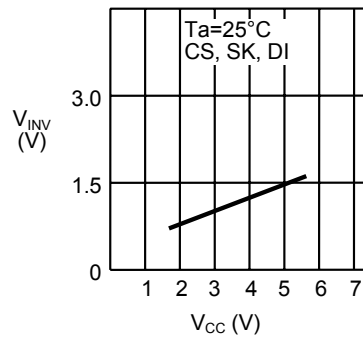
1.26 Low level output current I_{OL} —
Ambient temperature T_a



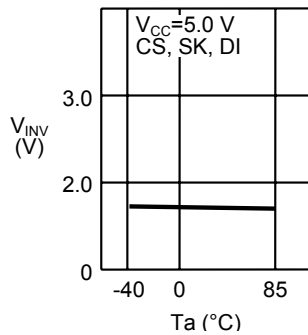
1.27 Low level output current I_{OL} —
Ambient temperature T_a



1.28 Input voltage $V_{IN}(V_{IL}, V_{IH})$ —
Power supply voltage V_{CC}

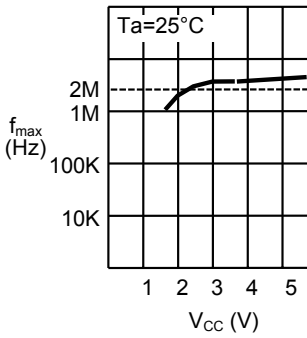


1.29 Input voltage $V_{IN}(V_{IL}, V_{IH})$ —
Ambient temperature T_a

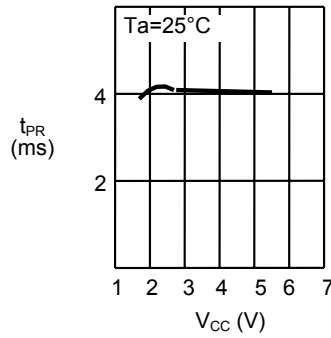


2. AC Characteristics

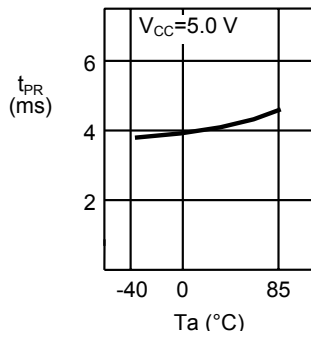
2.1 Maximum operating frequency f_{max} —
Power supply voltage V_{CC}



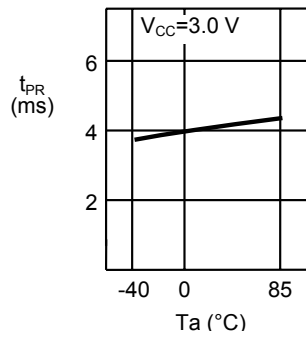
2.2 Program time t_{PR} —
Power supply voltage V_{CC}



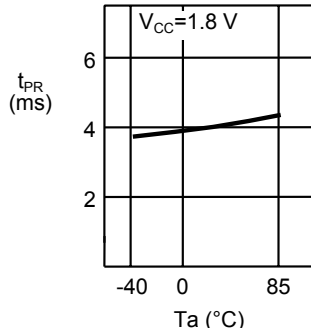
2.3 Program time t_{PR} —
Ambient temperature T_a



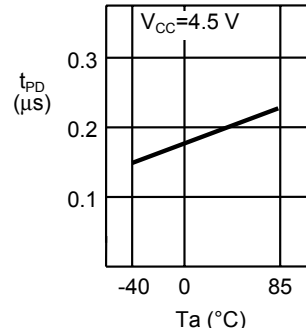
2.4 Program time t_{PR} —
Ambient temperature T_a



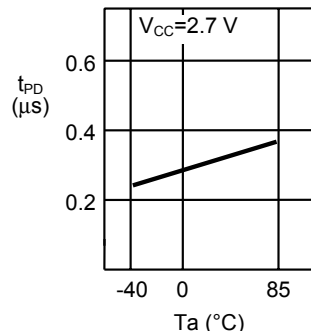
2.5 Program time t_{PR} —
Ambient temperature T_a



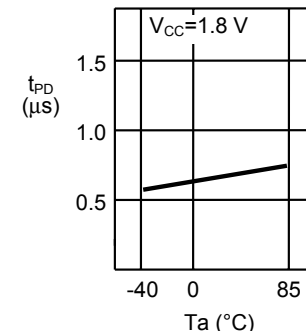
2.6 Data output delay time t_{PD} —
Ambient temperature T_a



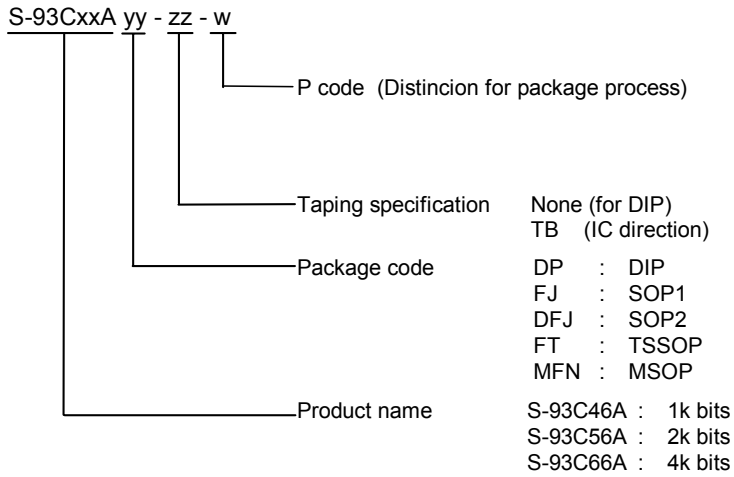
2.7 Data output delay time t_{PD} —
Ambient temperature T_a



2.8 Data output delay time t_{PD} —
Ambient temperature T_a



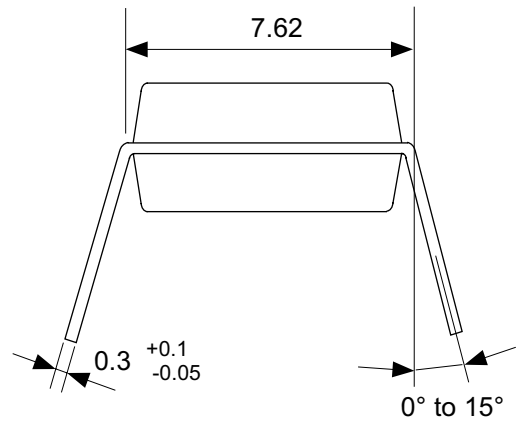
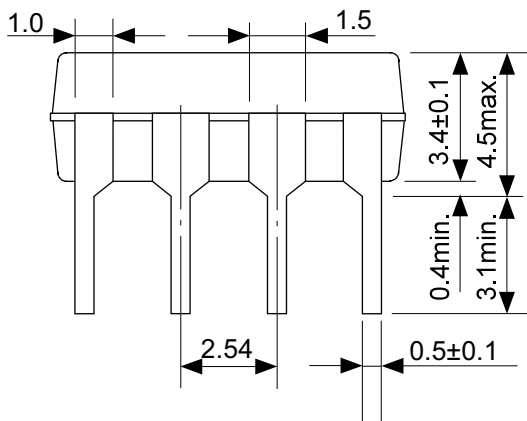
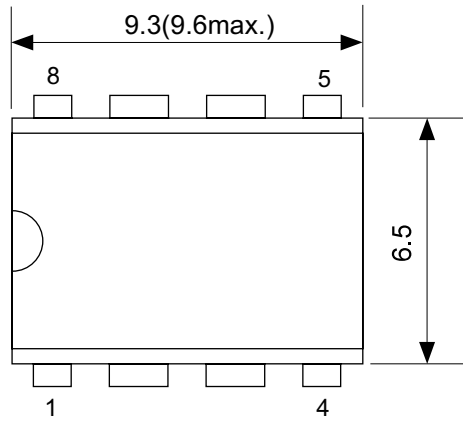
■ **Ordering Information**



Product name	Package code	Taping specification	Package/Tape/Reel drawings
S-93C46A S-93C56A S-93C66A	DP	None	DP008-A
	FJ	-TB	FJ008-D
	DFJ		FT008-E
	FT	-TB	FN008-A
	MFN	-TB	

Note

- 1) Package dimensions of SOPs whose package codes are FJ and DFJ are the same in the range of deviation.
- 2) Please contact an SII local office or a local representative for details.



No. DP008-A-P-SD-1.1

TITLE	DIP8-A-PKG Dimensions
No.	DP008-A-P-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	



No. FJ008-A-P-SD-2.1

TITLE	SOP8J-D-PKG Dimensions
No.	FJ008-A-P-SD-2.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	



Feed direction →

No. FJ008-D-C-SD-1.1

TITLE	SOP8J-D-Carrier Tape
No.	FJ008-D-C-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	

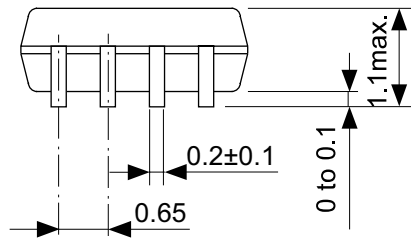


Enlarged drawing in the central part



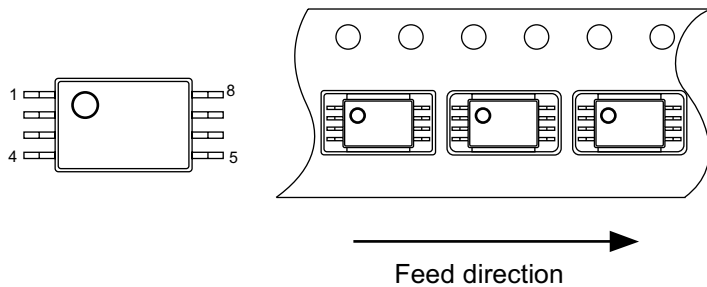
No. FJ008-D-R-SD-1.1

TITLE	SOP8J-D-Reel		
No.	FJ008-D-R-SD-1.1		
SCALE		QTY.	2,000
UNIT	mm		
Seiko Instruments Inc.			



No. FT008-A-P-SD-1.1

TITLE	TSSOP8-E-PKG Dimensions
No.	FT008-A-P-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	



No. FT008-E-C-SD-1.0

TITLE	TSSOP8-E-Carrier Tape
No.	FT008-E-C-SD-1.0
SCALE	
UNIT	mm
Seiko Instruments Inc.	

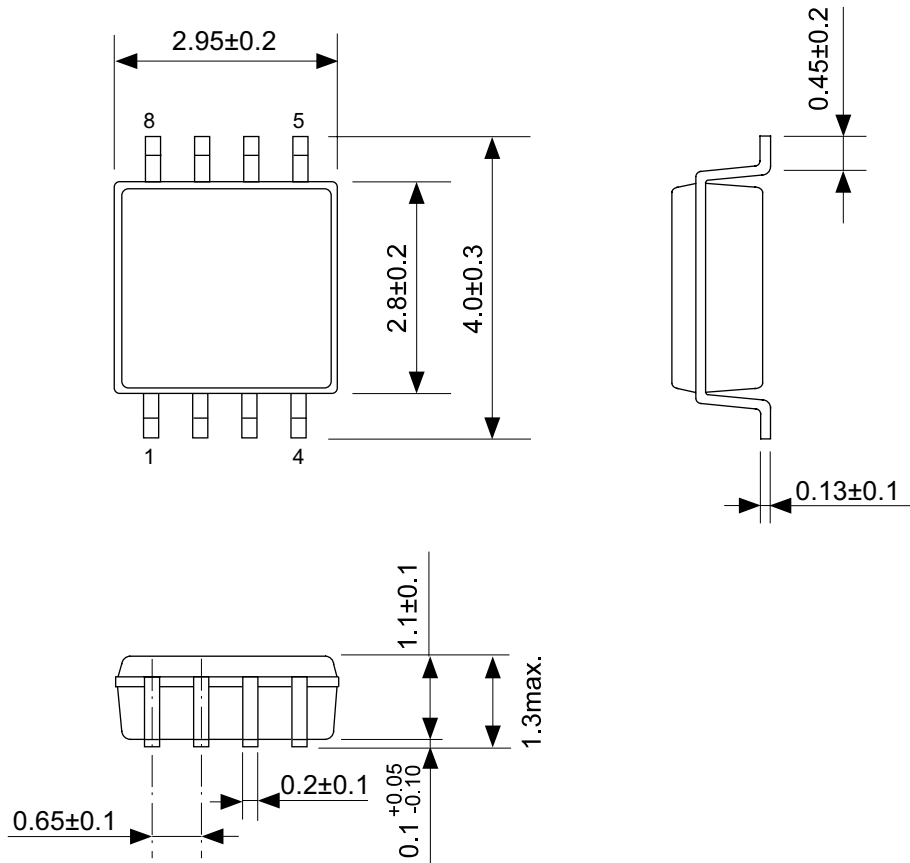


Enlarged drawing in the central part



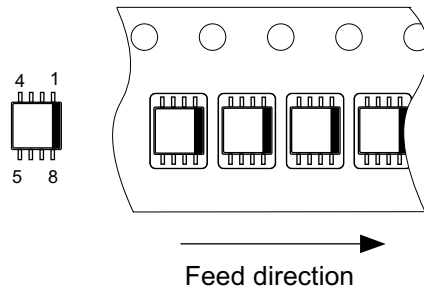
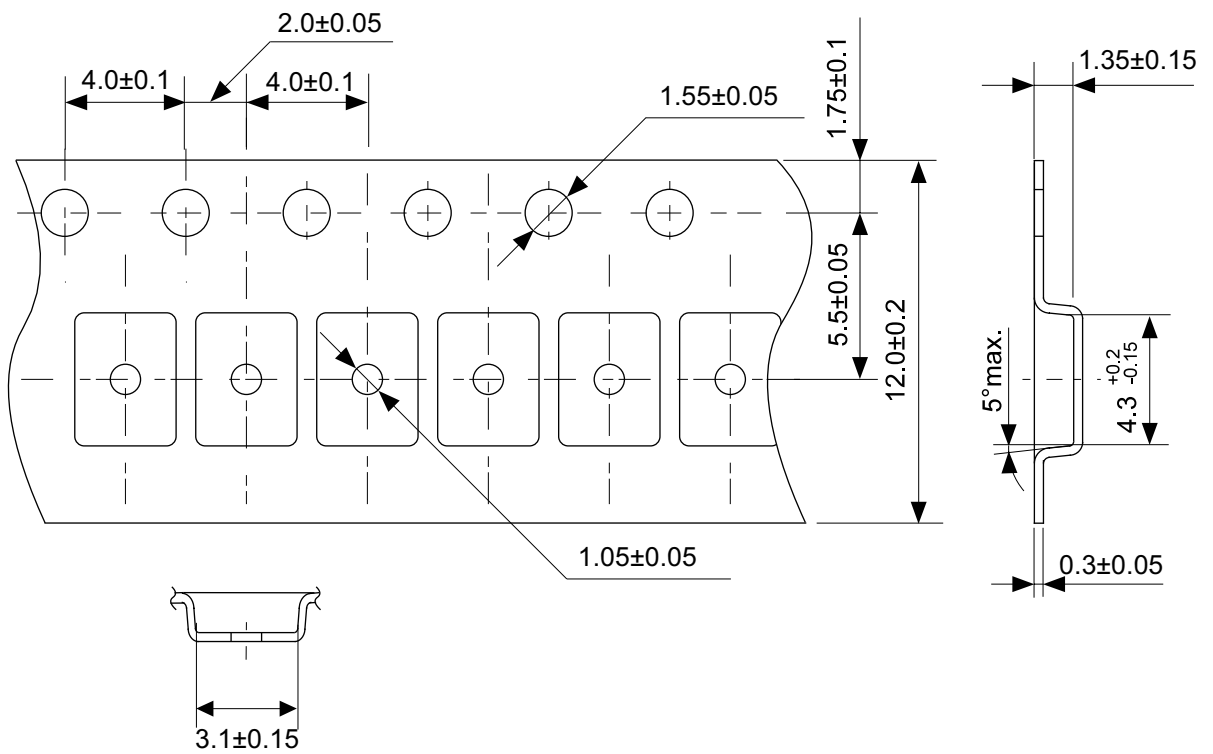
No. FT008-E-R-SD-1.0

TITLE	TSSOP8-E-Reel		
No.	FT008-E-R-SD-1.0		
SCALE		QTY.	3,000
UNIT	mm		
Seiko Instruments Inc.			



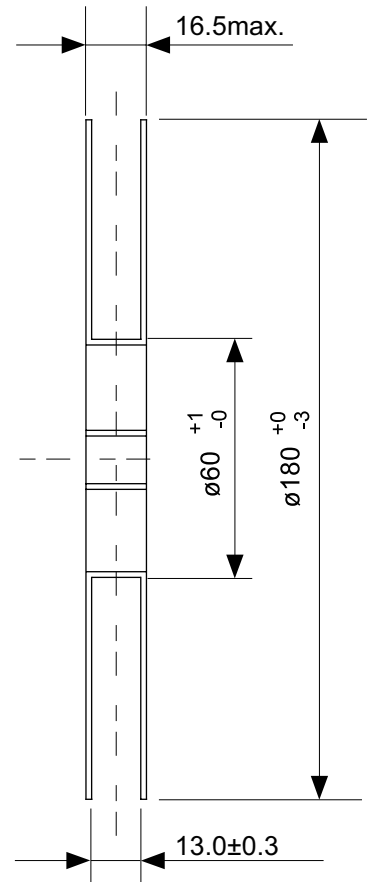
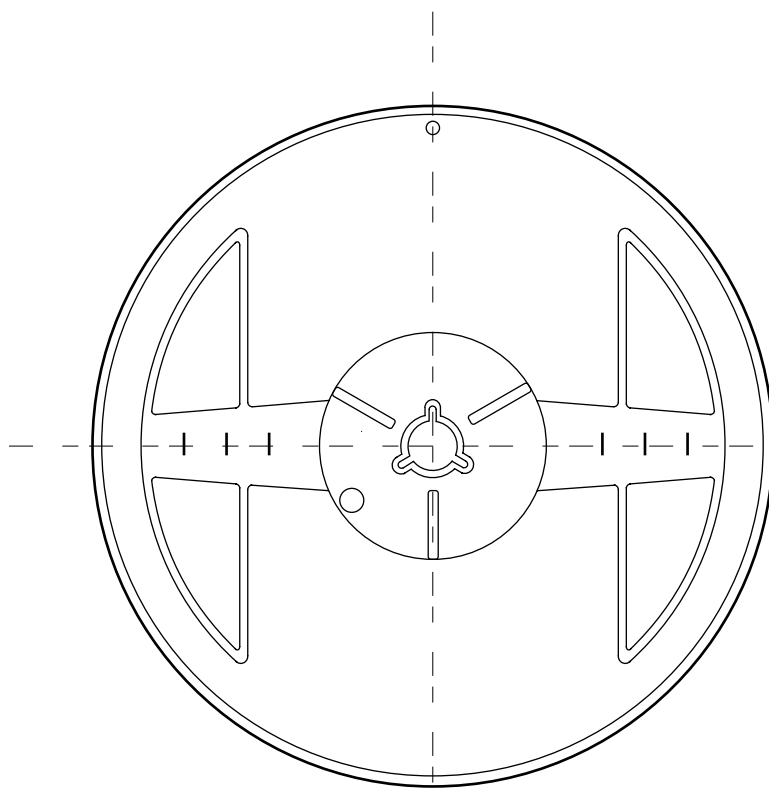
No. FN008-A-P-SD-1.1

TITLE	MSOP8-A-PKG Dimensions
No.	FN008-A-P-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	

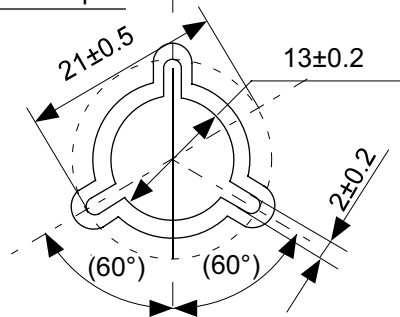


No. FN008-A-C-SD-1.1

TITLE	MSOP8-A-Carrier Tape
No.	FN008-A-C-SD-1.1
SCALE	
UNIT	mm
Seiko Instruments Inc.	



Enlarged drawing in the central part



No. FN008-A-R-SD-1.1

TITLE	MSOP8-A-Reel		
No.	FN008-A-R-SD-1.1		
SCALE		QTY.	3,000
UNIT	mm		
Seiko Instruments Inc.			

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